

N-Channel 20-V (D-S) MOSFET

PRODUCT SUMMARY		
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A)
20	0.033 at V _{GS} = 4.5 V	4.9
	0.040 at V _{GS} = 2.5 V	4.4
	0.051 at V _{GS} = 1.8 V	3.9

FEATURES

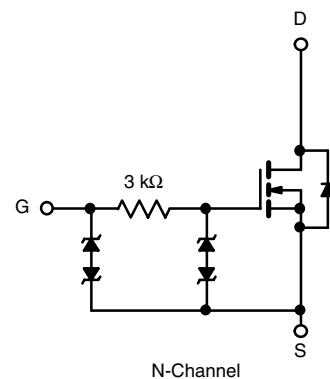
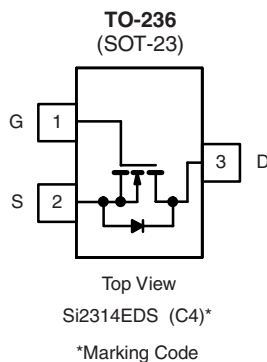
- Halogen-free According to IEC 61249-2-21 Available
- TrenchFET® Power MOSFET
- ESD Protected: 3000 V



RoHS
COMPLIANT
HALOGEN
FREE
Available

APPLICATIONS

- LI-Ion Battery Protection



Ordering Information: Si2314EDS-T1-E3 (Lead (Pb)-free)
Si2314EDS-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted					
Parameter	Symbol	5 s	Steady State	Unit	
Drain-Source Voltage	V _{DS}	20		V	
Gate-Source Voltage	V _{GS}	± 12			
Continuous Drain Current (T _J = 150 °C) ^a	I _D	T _A = 25 °C	4.9	3.77	A
		T _A = 70 °C	3.9	3.0	
Pulsed Drain Current ^b	I _{DM}	15			
Avalanche Current ^b	I _{AS}	L = 0.1 mH	15		
Single Avalanche Energy			E _{AS}	11.25	
Continuous Source Current (Diode Conduction) ^a	I _S	1.0		A	
Power Dissipation ^a	P _D	T _A = 25 °C	1.25	0.75	W
		T _A = 70 °C	0.80	0.48	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^a	R _{thJA}	t ≤ 5 s	75	100	°C/W
		Steady State	120	166	
Maximum Junction-to-Foot	R _{thJF}	40	50		

Notes:
a. Surface Mounted on 1" x 1" FR4 board.
b. Pulse width limited by maximum junction temperature.



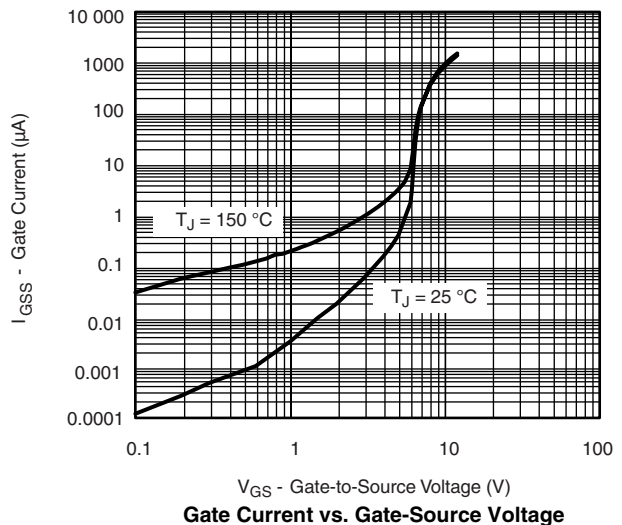
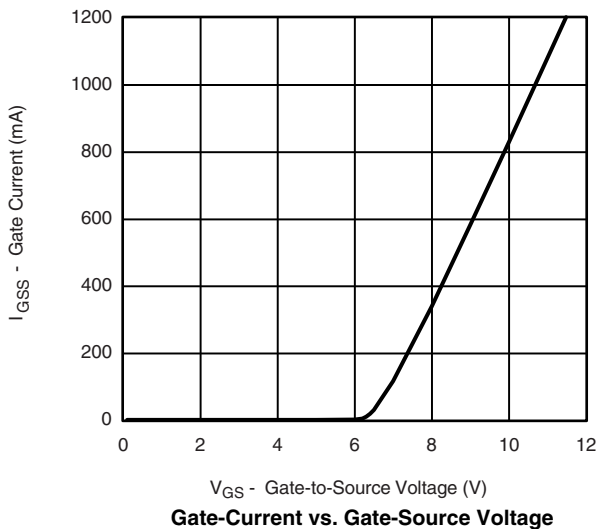
SPECIFICATIONS $T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Limits			Unit
			Min.	Typ.	Max.	
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	20			V
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	0.45		0.95	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 4.5\text{ V}$			± 1.5	μA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}, T_J = 70\text{ }^\circ\text{C}$			75	μA
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 10\text{ V}, V_{GS} = 4.5\text{ V}$	15			A
Drain-Source On-Resistance ^a	$R_{DS(on)}$	$V_{GS} = 4.5\text{ V}, I_D = 5.0\text{ A}$		0.027	0.033	Ω
		$V_{GS} = 2.5\text{ V}, I_D = 4.5\text{ A}$		0.033	0.040	Ω
		$V_{GS} = 1.8\text{ V}, I_D = 4.0\text{ A}$		0.042	0.051	Ω
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15\text{ V}, I_D = 5.0\text{ A}$		40		S
Diode Forward Voltage	V_{SD}	$I_S = 1.0\text{ A}, V_{GS} = 0\text{ V}$		0.8	1.2	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = 10\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 5.0\text{ A}$		11.0	14.0	nC
Gate-Source Charge	Q_{gs}			1.5		nC
Gate-Drain Charge	Q_{gd}			2.1		nC
Switching						
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 10\text{ V}, R_L = 10\text{ }\Omega$ $I_D \cong 1.0\text{ A}, V_{GEN} = 4.5\text{ V}, R_g = 6\text{ }\Omega$		0.53	0.8	μs
Rise Time	t_r			1.4	2.2	μs
Turn-Off Delay Time	$t_{d(off)}$			13.5	20	μs
Fall Time	t_f			5.9	9	μs
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = 1.0\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		13	25	ns

Notes:

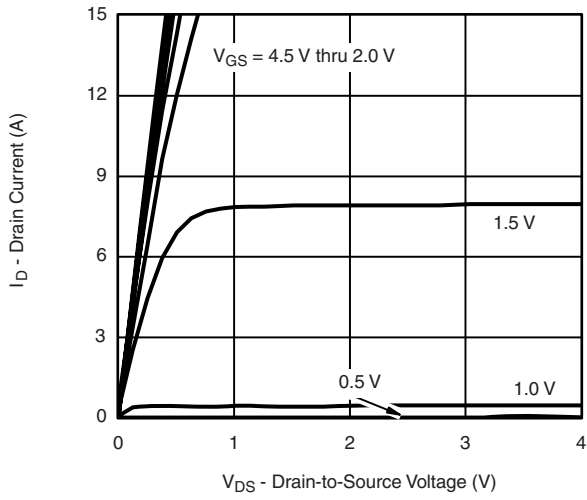
- a. Pulse test: $PW \leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

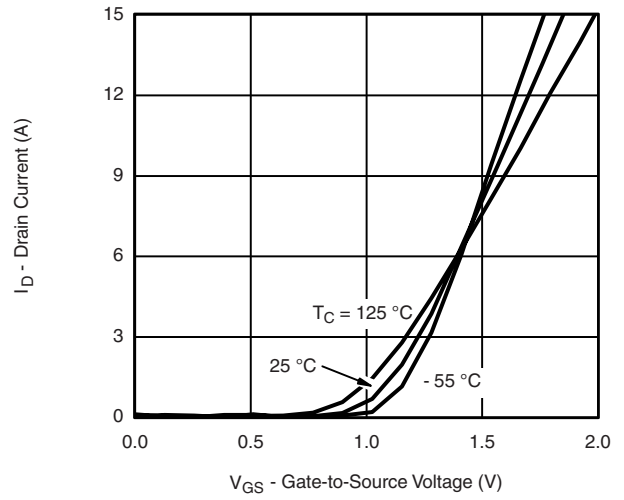
TYPICAL CHARACTERISTICS $25\text{ }^\circ\text{C}$, unless otherwise noted



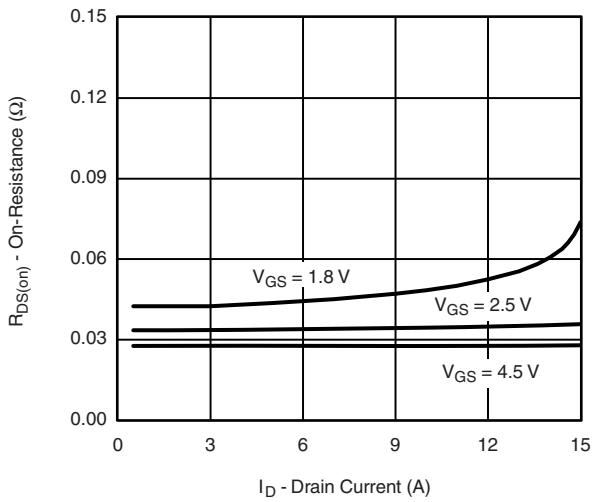
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



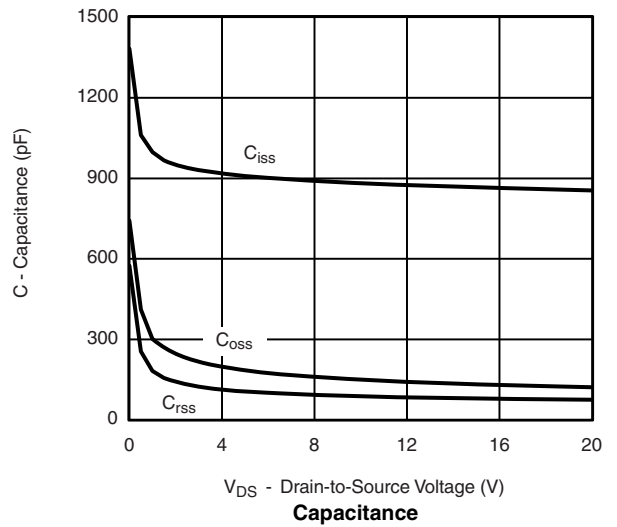
Output Characteristics



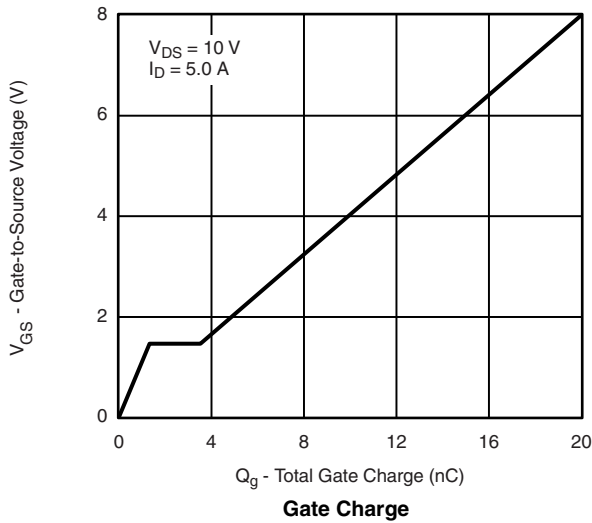
Transfer Characteristics



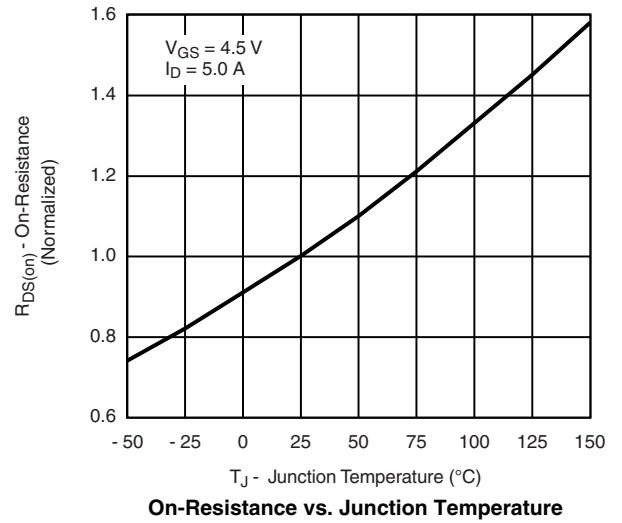
On-Resistance vs. Drain Current



Capacitance

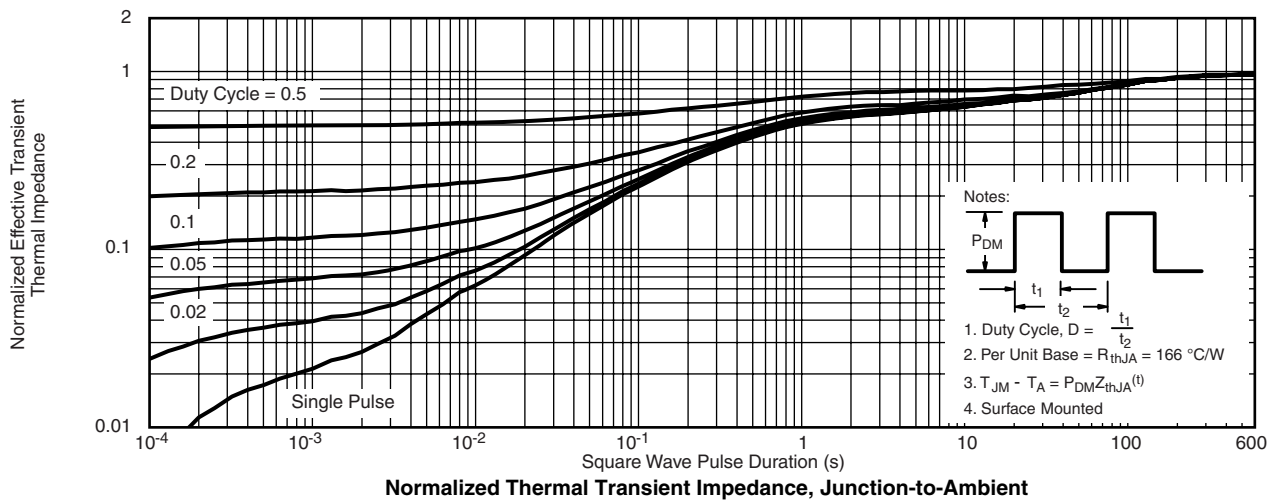
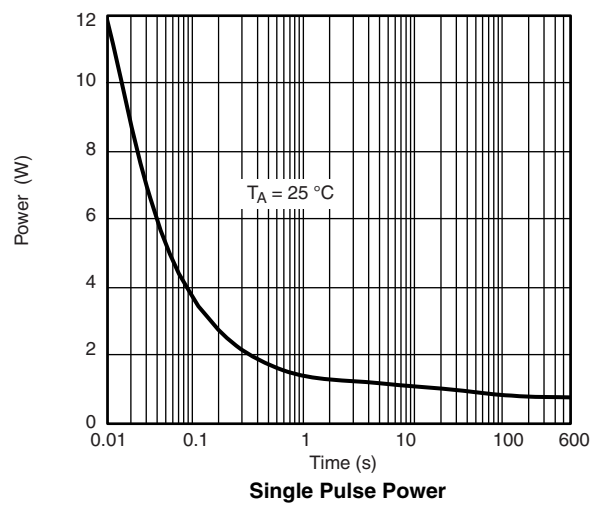
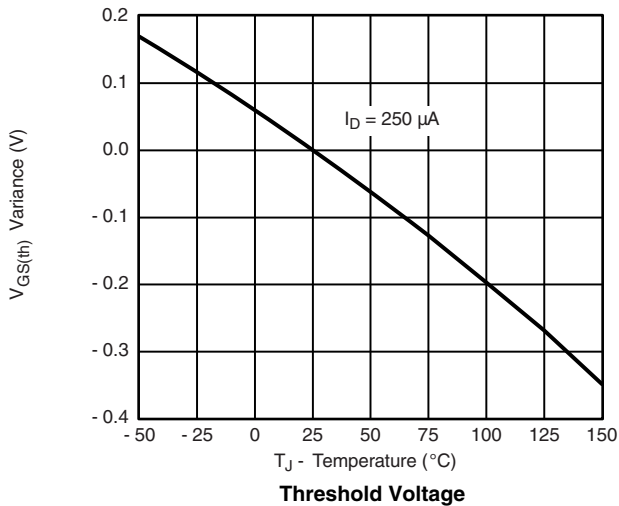
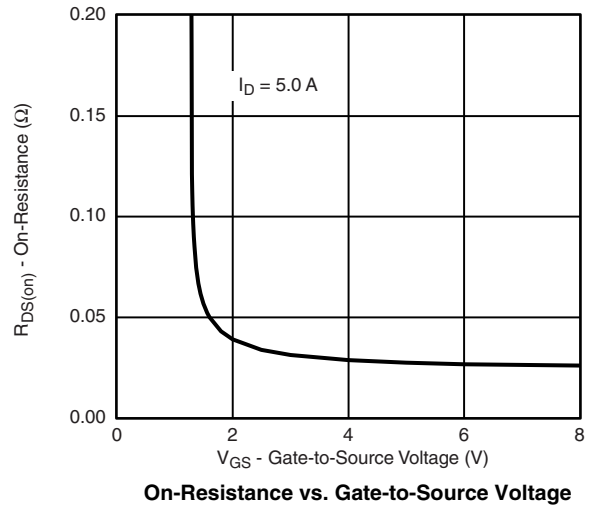
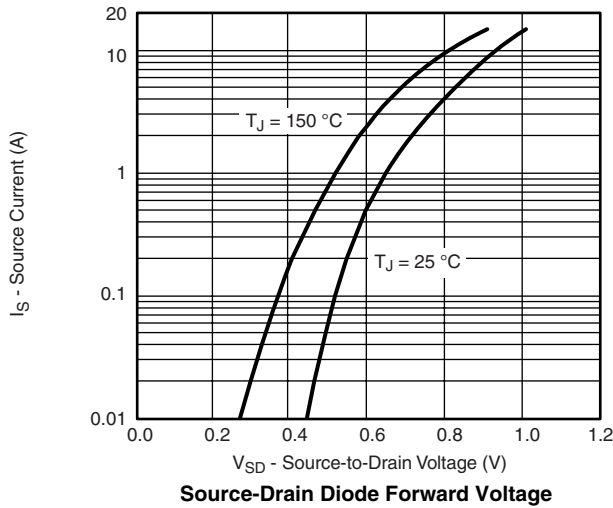


Gate Charge



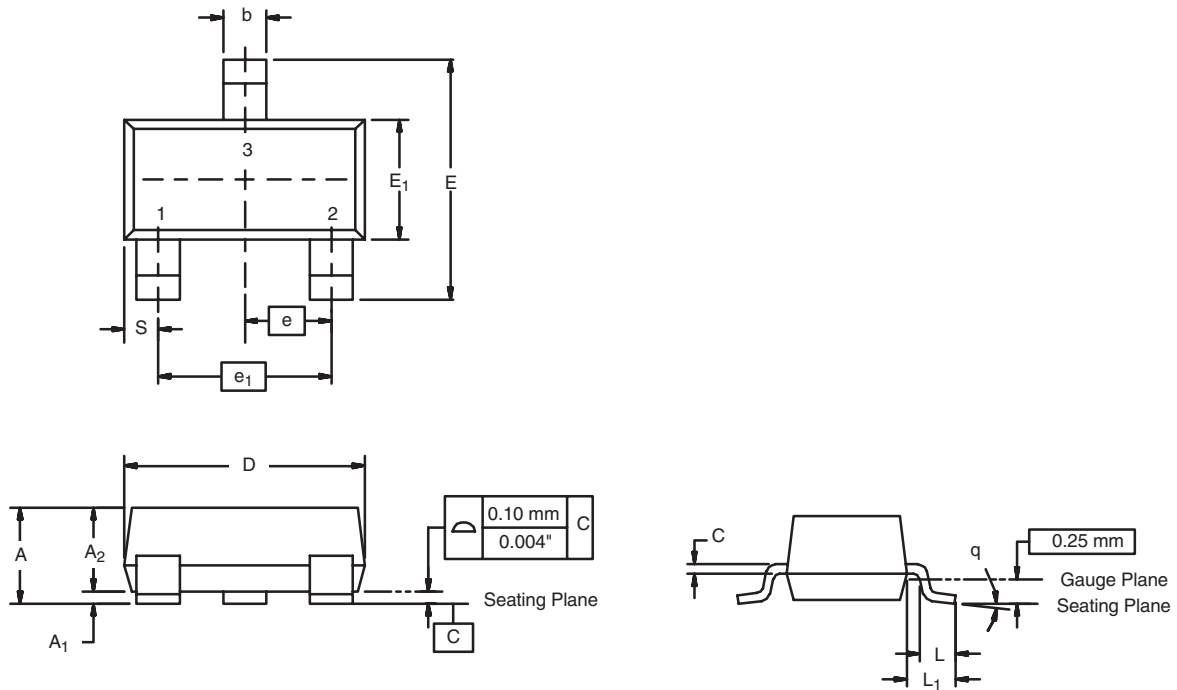
On-Resistance vs. Junction Temperature

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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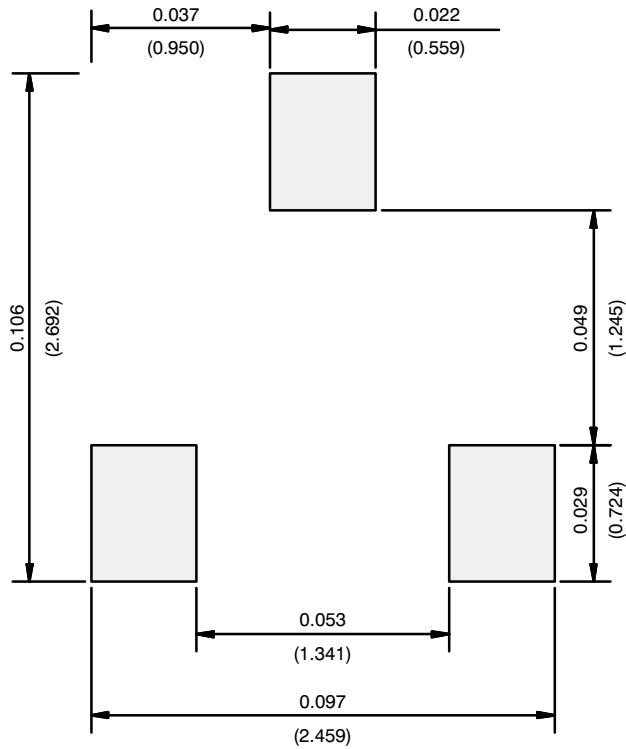
SOT-23 (TO-236): 3-LEAD



Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	0.89	1.12	0.035	0.044
A ₁	0.01	0.10	0.0004	0.004
A ₂	0.88	1.02	0.0346	0.040
b	0.35	0.50	0.014	0.020
c	0.085	0.18	0.003	0.007
D	2.80	3.04	0.110	0.120
E	2.10	2.64	0.083	0.104
E ₁	1.20	1.40	0.047	0.055
e	0.95 BSC		0.0374 Ref	
e ₁	1.90 BSC		0.0748 Ref	
L	0.40	0.60	0.016	0.024
L ₁	0.64 Ref		0.025 Ref	
S	0.50 Ref		0.020 Ref	
q	3°	8°	3°	8°

ECN: S-03946-Rev. K, 09-Jul-01
 DWG: 5479

RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads
Dimensions in Inches/(mm)

[Return to Index](#)



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